IN THE CLAIMS:

Please substitute the following listing of claims for the previous listing of claims.

1. (Previously presented) A method of cleaning a surface of a substrate processing chamber component to remove process deposits therefrom, the method comprising:

(a) cooling the surface comprising the process deposits to a temperature below about -40°C by at least one of (i) immersing the surface in liquid nitrogen, and (ii) spraying the surface with the liquid nitrogen,

thereby fracturing the process deposits on the surface.

2. (Original) A method according to claim 1 wherein the surface comprises a first thermal expansion coefficient and the process deposits comprise a second thermal expansion coefficient, and wherein the first thermal expansion coefficient is at least 2 times the second thermal expansion coefficient.

3-4. (Canceled)

5. (Currently amended) A method according to claim [[3]] 1 wherein (i) further comprises ~~comprising~~ ultrasonically agitating the surface.

6. (Original) A method according to claim 1 further comprising at least one of:

(b) grit blasting the surface; or

(c) cleaning the surface with a cleaning solution comprising HF and HNO_3.

7. (Original) A method according to claim 1 further comprising heating the surface to a temperature of at least about 150°C.

8. (Original) A method according to claim 7 further comprising, after heating the surface, flowing a cool fluid over the surface.

9. (Original) A component cleaned according to the method of claim 1, the component comprising a portion of one or more of an enclosure wall, a chamber shield, a target, a cover ring, a deposition ring, a support ring, an insulator ring, a coil, a coil support, a shutter disk, a clamp shield, and a substrate support; and

wherein the component is substantially absent process deposits.

10. (Original) A method according to claim 1 wherein the surface comprises a textured surface.

11. (Original) A method according to claim 1 wherein the surface comprises at least one of titanium, stainless steel, copper, tantalum and aluminum, and the process deposits comprise at least one of tantalum, tantalum nitride, titanium, titanium nitride, copper, aluminum, tungsten and tungsten nitride.

12-28. (Withdrawn)